





Certificate TH97/10561QM

Certificate TW00/17276EM

# GN2S

PRV: 700 Volts lo: 1.25 Amperes

### **FEATURES:**

- \* Glass passivated chip
- \* High current capability
- \* High reliability
- \* Low reverse current
- \* Low forward voltage drop
- \* Pb / RoHS Free

## **MECHANICAL DATA:**

\* Case : SMB Molded plastic

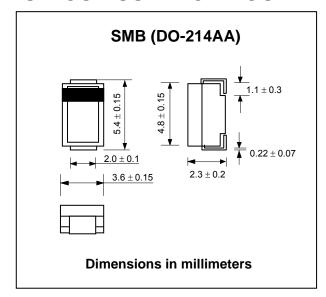
\* Epoxy: UL94V-O rate flame retardant

\* Lead: Lead Formed for Surface Mount

\* Polarity: Color band denotes cathode end

\* Mounting position : Any \* Weight : 0.1079 gram

# GLASS PASSIVATED JUNCTION SILICON SURFACE MOUNT



#### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25 °C ambient temperature unless otherwise specified. Single phase, half wave, 60 Hz, resistive or inductive load. For capacitive load, derate current by 20%.

RATING		SYMBOL	VALUE	UNIT
Maximum Repetitive Peak Reverse Voltage		$V_{RRM}$	700	V
Maximum RMS Voltage		V <sub>RMS</sub>	490	V
Maximum DC Blocking Voltage		V <sub>DC</sub>	700	V
Minimum Average Output Forward Curre	nt Ta = 25 °C		1.25	А
	Tc = 55 °C	Io	3.75	
Peak Forward Surge Current				
8.3ms Single half sine wave Superimposed		I <sub>FSM</sub>	80	Α
on rated load (JEDEC Method)				
Maximum Forward Voltage at $I_F$ = 2.0 A, Tc = 25 °C		$V_{F}$	1.0	V
Maximum DC Reverse Current	Ta = 25 °C	I <sub>R</sub>	2.0	μA
at rated DC Blocking Voltage	Ta = 100 °C	I <sub>R(H)</sub>	20	μA
Typical Junction Capacitance (Note1)		CJ	75	pF
Junction Temperature Range		T <sub>J</sub>	- 65 to + 150	°C
Storage Temperature Range		T <sub>STG</sub>	- 65 to + 150	°C

Note: (1) Measured at 1.0 MHz and applied reverse voltage of 4.0Vpc

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